

IN THE CLAIMS

Please amend Claim 1, to read as follows. Note that all the claims currently pending in this application, including those not presently amended, have been reproduced below for the Examiner's convenience.

1. (Currently Amended) A method for making a through-hole in a silicon substrate comprising the steps of:
 - forming a high-impurity-concentration region at a first surface of the silicon substrate that continuously surrounds only the periphery of a through-hole-forming region;
 - forming an etching stop layer over the through-hole-forming region and the high-impurity-concentration region;
 - forming a mask layer having an opening on a second surface of the silicon substrate, the second surface being opposite to the first surface;
 - etching the silicon substrate at the opening through the mask layer until the etching stop layer is exposed to the second surface, while the high-impurity-concentration region is not exposed to the second surface;
 - subsequently, further etching the silicon substrate until the etched portion extends to the high-impurity-concentration region; and
 - removing the etching stop layer at least at the portion exposed to the second surface.

2. (Original) A method for making a through-hole according to Claim 1, wherein the high-impurity-concentration region has an impurity concentration of $1 \times 10^{19}/\text{cm}^3$ or more.

3. (Original) A method for making a through-hole according to Claim 2, wherein the high-impurity-concentration region has an impurity concentration of $7 \times 10^{19}/\text{cm}^3$ or more.

4. (Original) A method for making a through-hole according to Claim 1, wherein the impurity is selected from the group consisting of boron, phosphorus, arsenic, and antimony.

5. (Original) A method for making a through-hole according to Claim 1, wherein the high-impurity-concentration region has a width of 1 to 20 μm and a depth of 1 to 3 μm .

6. (Original) A method for making a through-hole according to Claim 1, wherein the high-impurity-concentration region is formed by forming an impurity diffusion layer in the first surface of the silicon substrate.

7. (Original) A method for making a through-hole according to Claim 1, wherein the etching stop layer comprises a silicon nitride film formed by low-pressure vapor deposition (LP-SiN).

8. (Withdrawn) An ink-jet printer head comprising an ink supply port fabricated by a method for making a through-hole according to any one of Claims 1 to 7.